



N 沟道增强型场效应晶体管  
N-CHANNEL MOSFET

# MT04N004B

## 主要参数 MAIN CHARACTERISTICS

ID	140A
V <sub>DSS</sub>	40V
R <sub>dson-max</sub> (@V <sub>gs</sub> =10V)	4. 0mΩ
Q <sub>g-typ</sub>	72. 7nC

## 用途

- 高功率 DC/DC 转换与功率开关
- 直流电机控制
- 不间断电源

## APPLICATIONS

- High power DC/DC converters and switch mode power supplies
- DC motor control
- Uninterruptible power supply

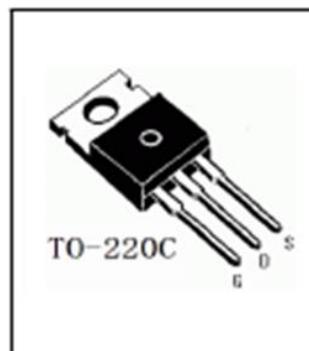
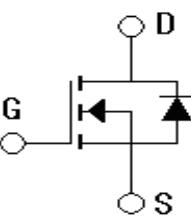
## 产品特性

- 低栅极电荷
- 低 R<sub>dson</sub>
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

## FEATURES

- Low gate charge
- Low R<sub>dson</sub>
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes				印记 Marking	封装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
MT04N004B-C-B	MT04N004B-C-BR	N/A	N/A	MT04N004B	TO-220C



MT04N004B

绝对最大额定值 ABSOLUTE RATINGS (T<sub>c</sub>=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		MT04N004B	
最高漏极—源极直流电压 Drain-Source Voltage	V <sub>DSS</sub>	40	V
连续漏极电流 Drain Current -continuous	I <sub>D</sub> T=25°C	140*	A
	I <sub>D</sub> T=100°C	99*	A
最大脉冲漏极电流 (注 1) Drain Current - pulse (note 1)	I <sub>DM</sub>	560*	A
最高栅源电压 Gate-Source Voltage	V <sub>GSS</sub>	±20	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	144	mJ
耗散功率 Power Dissipation	P <sub>D</sub> T <sub>c</sub> =25°C -Derate above 25°C	108.7	W
		0.87	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300	°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature



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## 电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最 小 Min	典 型 Typ	最 大 Max	单 位 Units
<b>关态特性 Off -Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	40	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V, V_{GS}=0V, T_C=25^\circ C$	-	-	1	$\mu A$
		$V_{DS}=32V, V_{GS}=0V, T_C=100^\circ C$	-	-	150	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS} = 20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS} = -20V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.2	-	3.8	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D=56A$	-	3.0	4.0	$m\Omega$
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS} = 0V, f=1.0MHz$	-	3150	-	pF
输出电容 Output capacitance	$C_{oss}$		-	429	-	pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	331	-	pF



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## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V,I <sub>D</sub> =30A,R <sub>G</sub> =2.7Ω (note 3, 4)	-	21.8	-	ns	
上升时间 Turn-On rise time	t <sub>r</sub>		-	83.4	-	ns	
延迟时间 Turn-Off delay time	t <sub>d(off)</sub>		-	49.8	-	ns	
下降时间 Turn-Off Fall time	t <sub>f</sub>		-	25.8	-	ns	
栅极电荷总量 Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V , I <sub>D</sub> =56A V <sub>GS</sub> =10V (note 3, 4)	-	72.7	-	nC	
栅一源电荷 Gate-Source charge	Q <sub>gs</sub>		-	21.5	-	nC	
栅一漏电荷 Gate-Drain charge	Q <sub>gd</sub>		-	26.5	-	nC	
漏一源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流	I <sub>S</sub>		-	-	140	A	
Maximum Continuous Drain -Source Diode Forward Current	I <sub>SM</sub>		-	-	560	A	
正向最大脉冲电流	I <sub>SM</sub>		-	-	560	A	
正向压降	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =56A	-	-	1.2	V	
Drain-Source Diode Forward Voltage			-	-	1.2	V	
反向恢复时间	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =56A dI <sub>F</sub> /dt=100A/μs (note 3)	-	26.3	-	ns	
Reverse recovery charge	Q <sub>rr</sub>		-	16.5	-	nC	

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最 大 Max		单 位 Unit
		MT04N004B		
结到管壳的热阻	R <sub>th(j-c)</sub>	1.15		°C/W
Thermal Resistance, Junction to Case				
结到环境的热阻	R <sub>th(j-A)</sub>	56		°C/W
Thermal Resistance, Junction to Ambient				

注释:

- 1: 脉冲宽度由最高结温限制  
 2: L=0.08mH, V<sub>GS</sub>=10V, R<sub>G</sub>=50Ω, I<sub>AS</sub>=60A 起始结温  
     T<sub>J</sub>=25°C  
 3: 脉冲测试: 脉冲宽度≤300μs, 占空比≤2%  
 4: 基本与工作温度无关

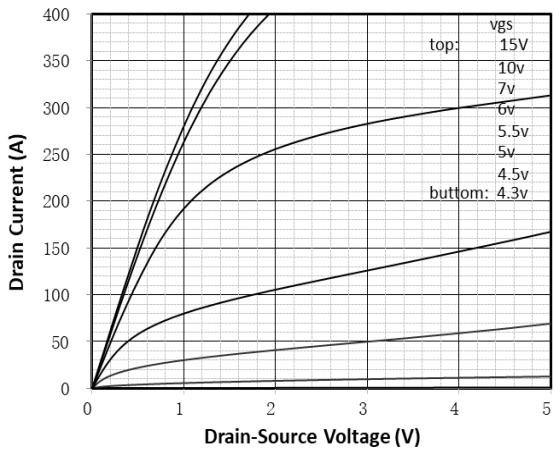
Notes:

- 1: Pulse width limited by maximum junction temperature  
 2: L=0.08mH, V<sub>GS</sub>=10V, R<sub>G</sub>=50Ω, I<sub>AS</sub>=60A, Starting T<sub>J</sub>=25°C  
 3: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%  
 4: Essentially independent of operating temperature

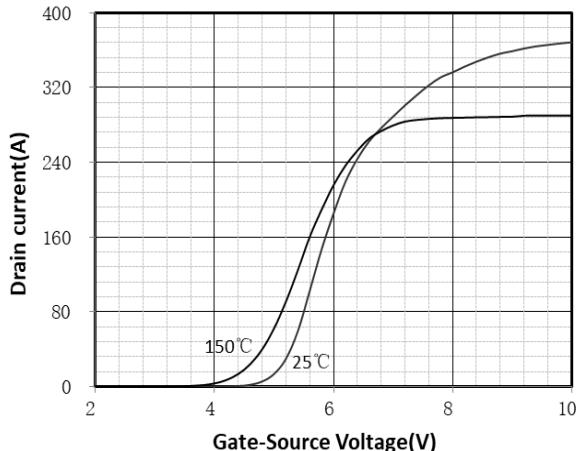


## 特征曲线 ELECTRICAL CHARACTERISTICS (curves)

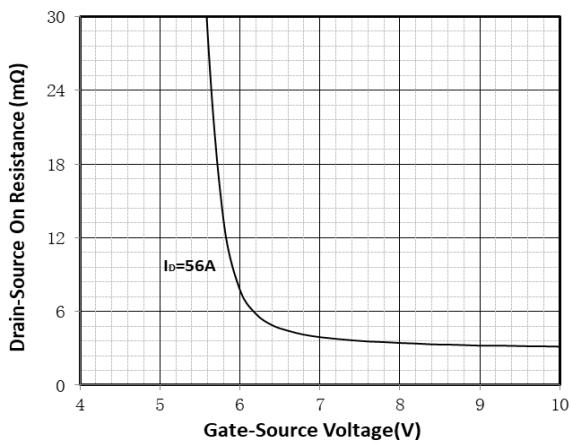
## On-Region Characteristics



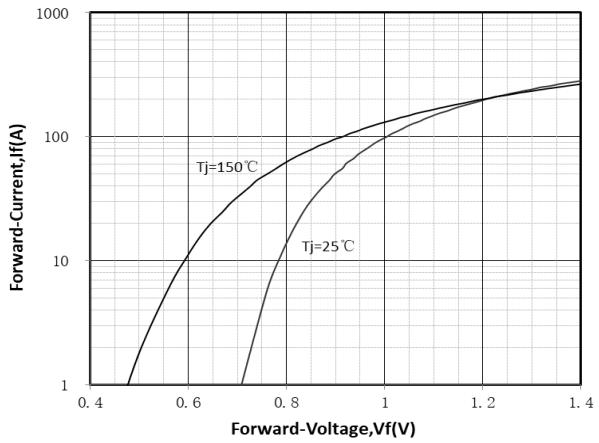
## Transfer Characteristics



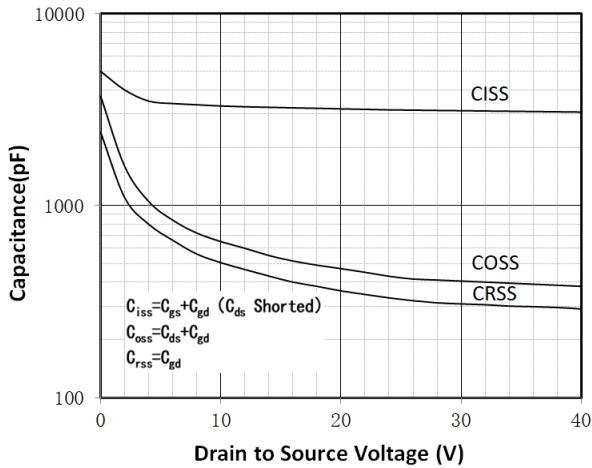
## On-Resistance Variation vs. Drain Current and Gate Voltage



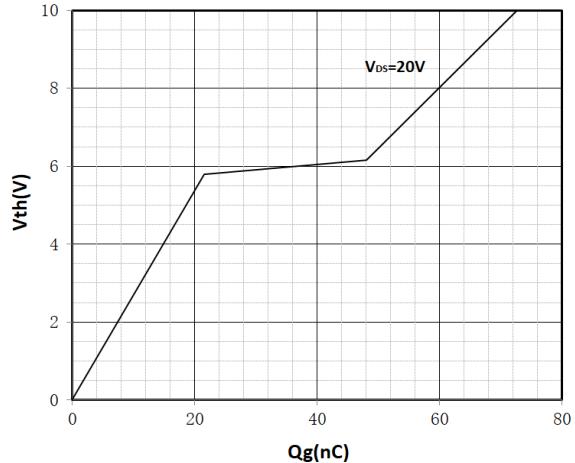
## Body Diode Forward Voltage Variation vs. Source Current and Temperature



## Capacitance Characteristics



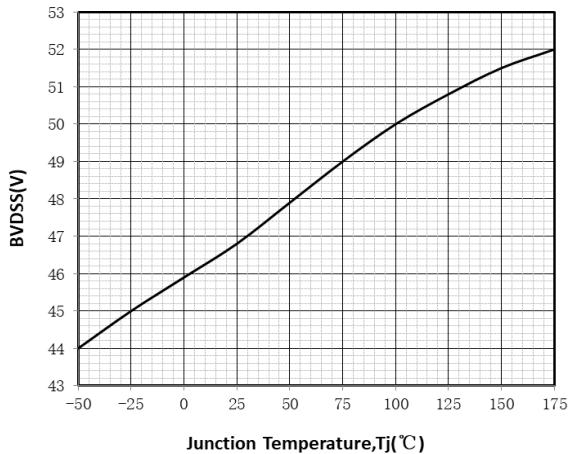
## Gate Charge Characteristics



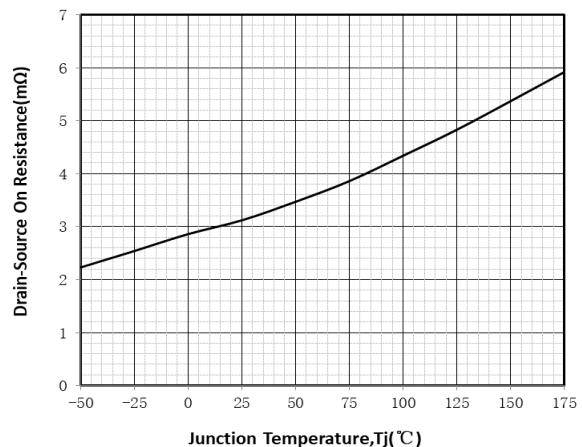


## 特征曲线 ELECTRICAL CHARACTERISTICS (curves)

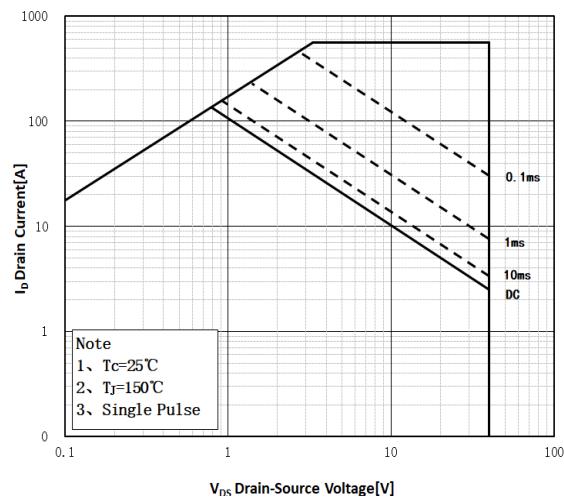
Breakdown Voltage Variation vs. Temperature



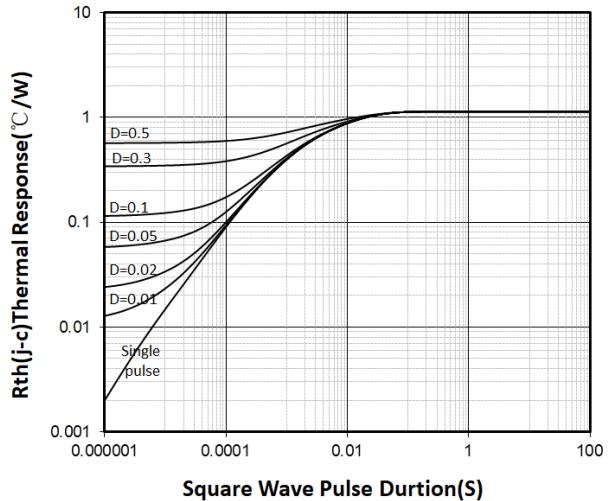
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area



Transient Thermal Response Curve



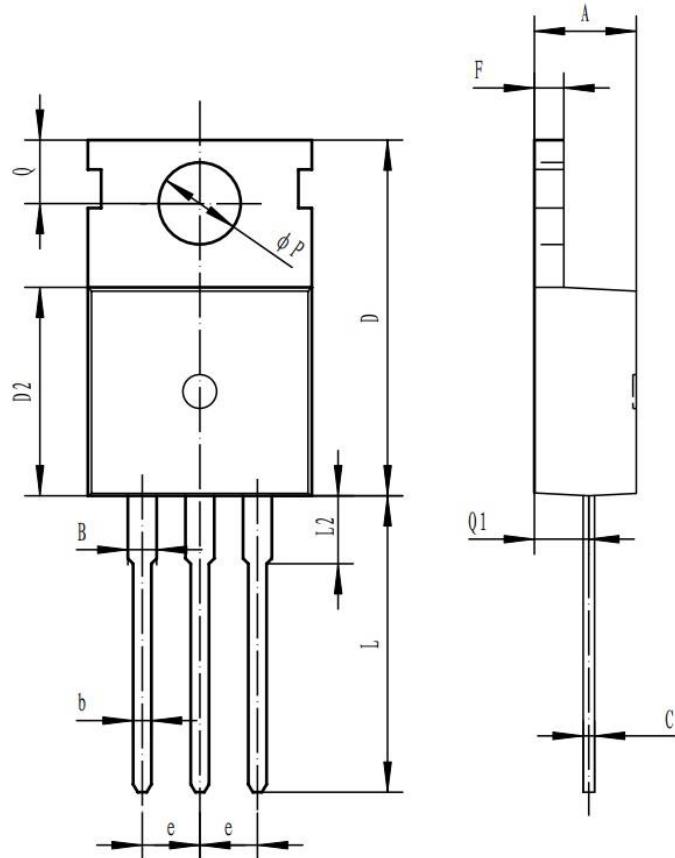


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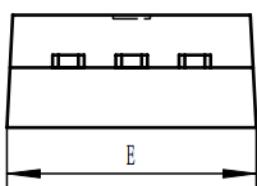
## 外形尺寸 PACKAGE MECHANICAL DATA

TO-220C

单位 Unit: mm



符号 symbol	MIN	MAX
A	4.30	4.70
B	1.22	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80





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